

中功率放大三极管 Medium Power Transistor(PNP)

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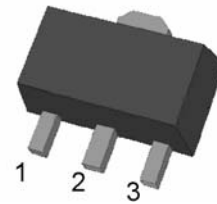
中功率放大三极管

FHBCX53

DESCRIPTION & FEATURES 概述及特点

- 1) For AF driver and output stages
- 2) High collector current
- 3) Low Collector-Emitter Saturation Voltage
- 4) Complement types: FHBCX56(NPN)

SOT-89



PIN ASSIGNMENT 引脚说明

PIN NAME 管脚符号	PIN NUMBER 引脚序号	FUNCTION 功能
	SOT-89	
B	1	BASE
C	2	COLLECTOR
E	3	EMITTER

MAXIMUM RATINGS(T_a=25°C) 最大额定值

CHARACTERISTIC 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Collector-Emitter Voltage 集电极-发射极电压	V _{CEO}	-80	Vdc
Collector-Base Voltage 集电极-基极电压	V _{CBO}	-100	Vdc
Emitter-Base Voltage 发射极-基极电压	V _{EBO}	-5	Vdc
Collector Current(DC) 集电极电流-直流	I _C	-1	Adc
Peak Collector Current 集电极峰值电流	I _{CM}	-1.5	Adc
Base Current 基极电流	I _B	100	mA
Peak Base Current 基极峰值电流	I _{BM}	200	mA
Total Power Dissipation 耗散功率	P _{tot}	1	W
Junction and Storage Temperature 结温和储存温度	T _J T _{stg}	150 , -55 ~150	°C

DEVICE MARKING 打标

FHBCX53=AH(40~250)

ELECTRICAL CHARACTERISTICS 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Test Condition 测试条件	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Emitter Breakdown Voltage 集电极-发射极击穿电压	V _{(BR)CEO}	I _C =-10mA,	-80	—	—	V
Collector-Base Breakdown Voltage 集电极-基极击穿电压	V _{(BR)CBO}	I _C =-100μA	-100	—	—	V
Emitter-Base Breakdown Voltage 发射极-基极击穿电压	V _{(BR)EBO}	I _E =-10μA	-5.0	—	—	V
Collector Cutoff Current 集电极截止电流	I _{CBO}	V _{CB} =-30V, I _E =0	—	—	-100	nA
Emitter Cutoff Current 发射极截止电流	I _{EBO}	V _{EB} =-4V, I _C =0	—	—	-20	nA
DC Current Gain 直流电流增益	h _{FE}	V _{CE} =-2V, I _C = -150mA	40	—	250	
Collector-Emitter Saturation Voltage 集电极-发射极饱和压降	V _{CE(sat)}	I _C =-500mA, I _B =-50mA	—	—	500	mV
Transition Frequency 特征频率	f _T	V _{CE} =-10V, I _C =-50mA, f=20MHZ	—	125	—	MHz